

1 Introduction

Resistive detector designs utilize materials with finite conductivity to achieve enhanced robustness or improved their performance. We employ a Finite Element Method (FEM) approach in conjunction with Garfield++ [1] to simulate induced signals across a wide range of devices in this category:

- Multi-gap Resistive Plate Chambers (MRPCs)
- μ -Resistive WELL
- Resistive Micromegas (ATLAS NSW MM, PICOSEC)
- Resistive Silicon Detectors (RSDs)
- 4D Diamond Sensor

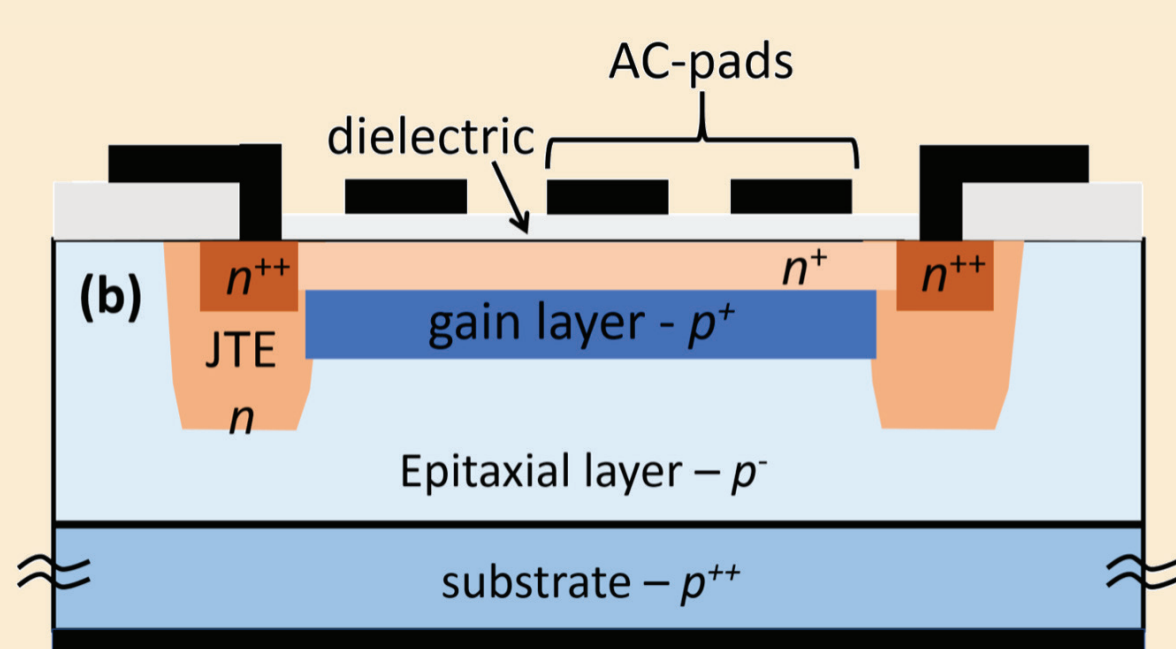


Fig. 1: Resistive silicon detector [2].

2 Dynamic weighting potential

The works of W. Shockley [3] and S. Ramo [4] describe the induction of current on grounded electrodes from moving charge carriers by using static so-called weighting potentials, defined by removing the drifting charges and applying a

constant voltage on the electrode under study while keeping all others grounded. Due to the medium's finite conductivity, these weighting potentials become time-dependent for geometries containing resistive materials [5,6].

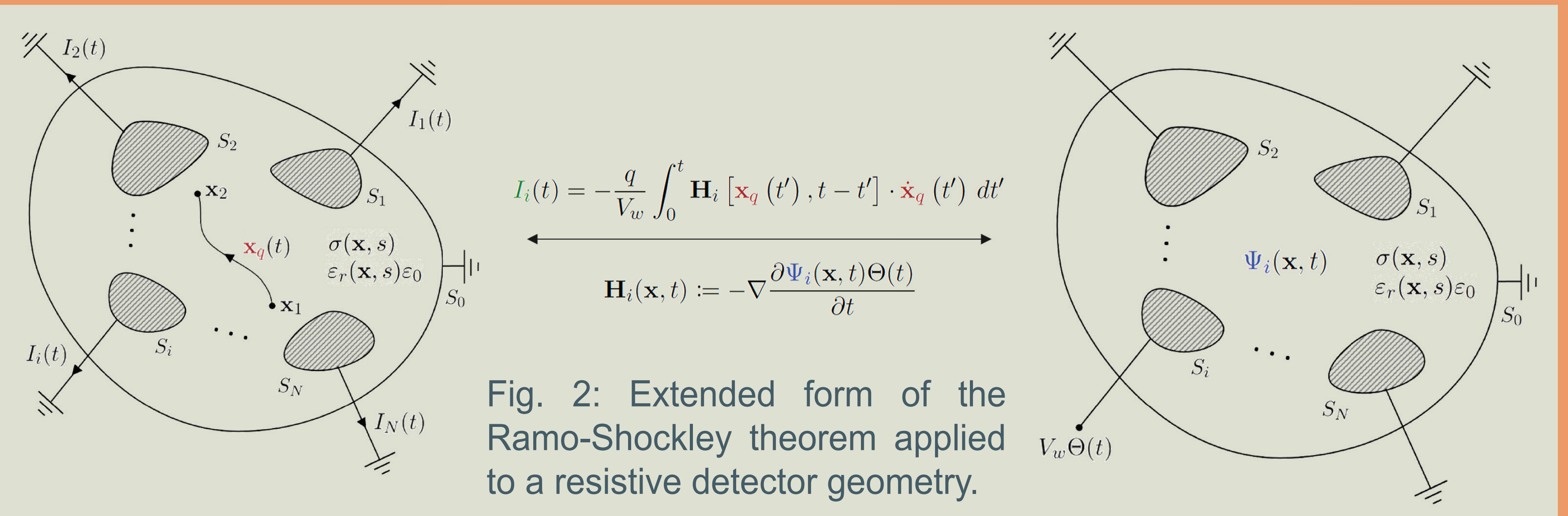


Fig. 2: Extended form of the Ramo-Shockley theorem applied to a resistive detector geometry.

3 Simulation methodology

We developed a numerical method to model the time dependence of the signals in resistive readout structures by employing a FEM solver [7].

Garfield++ then uses the resulting weighting potentials to calculate the signal on the electrodes induced by the drifting charge carriers [8].

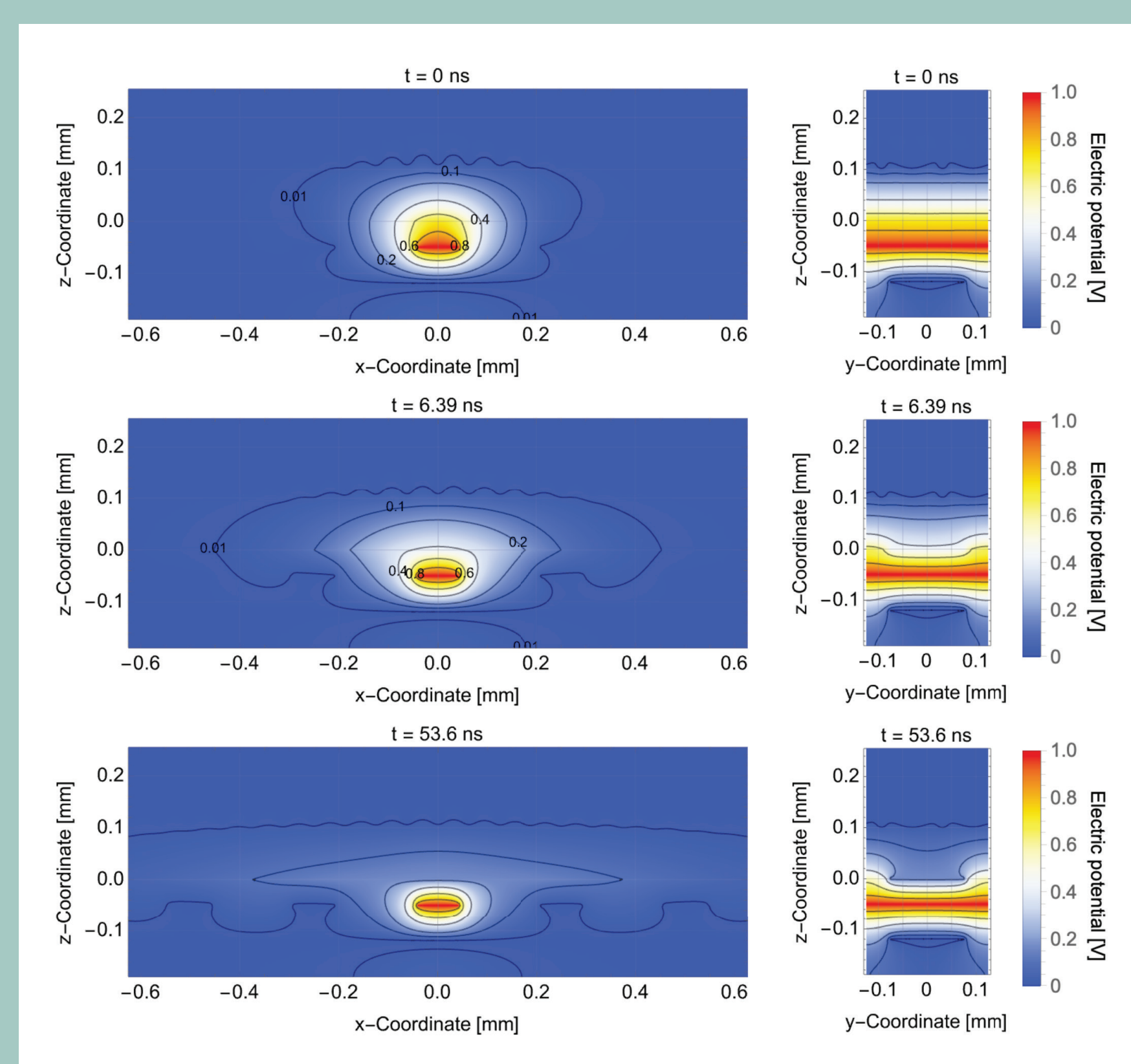
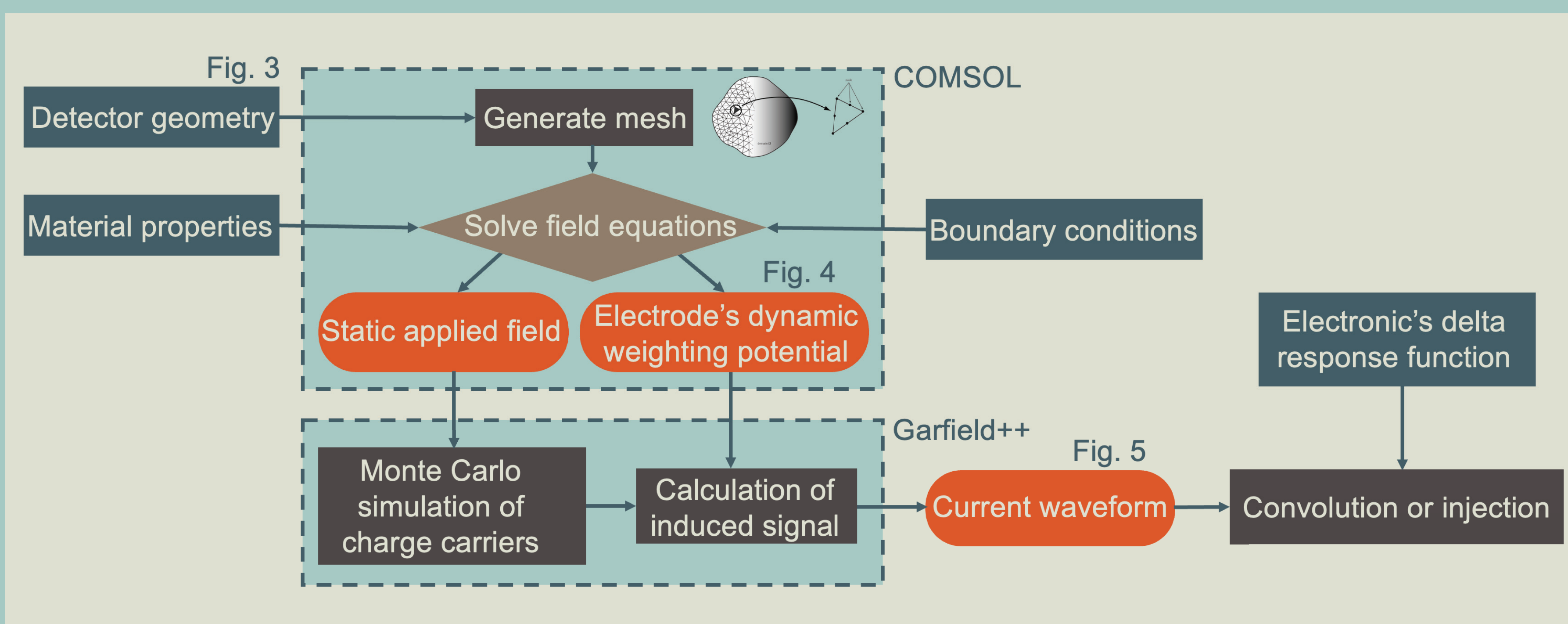


Fig. 4: Time slices of the dynamic weighting potential cross-sections of an x-strip electrode in the xz-plane (left) and yz-plane (right).

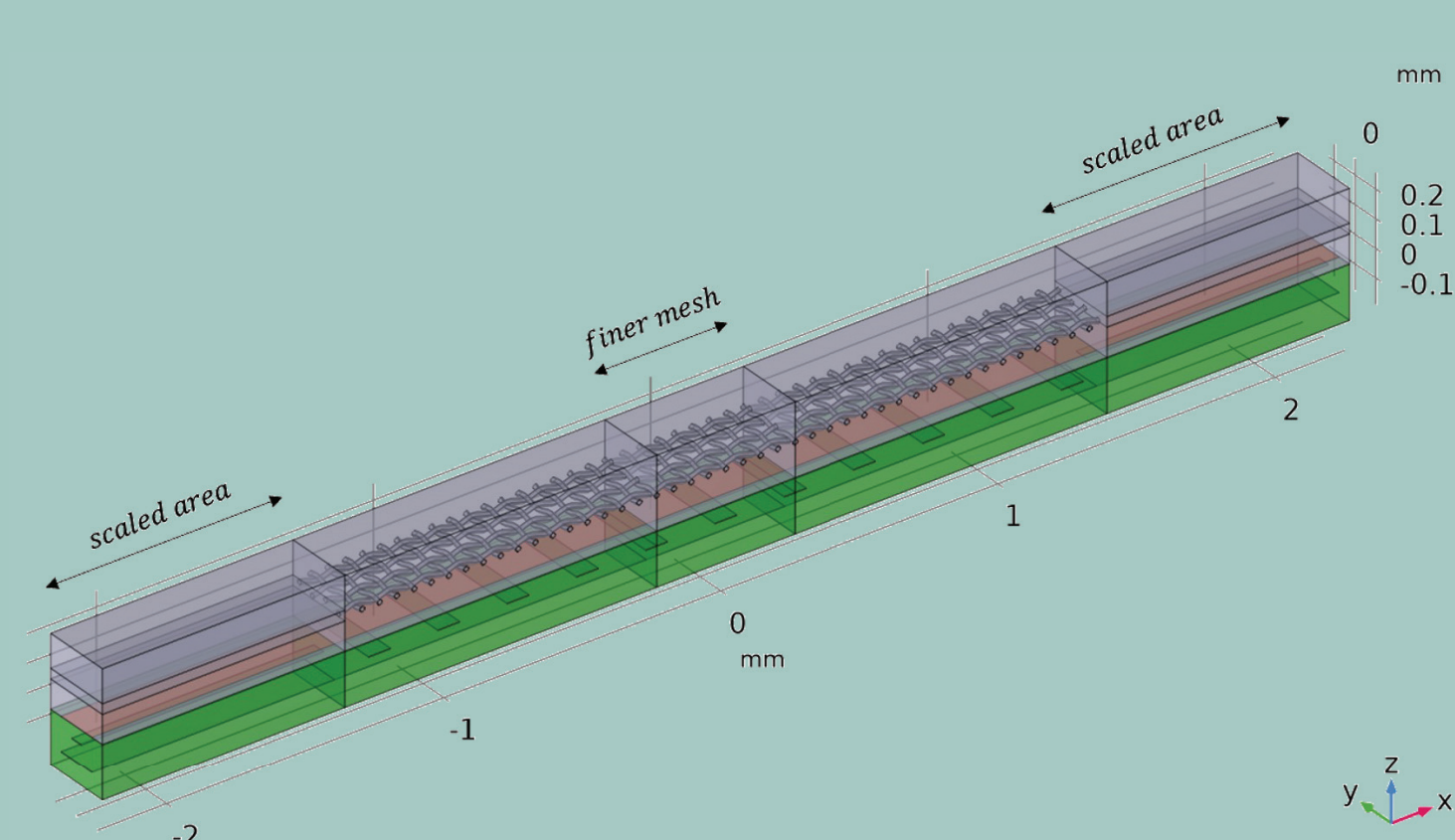


Fig. 3: Model of a 2D-readout resistive strip MM.

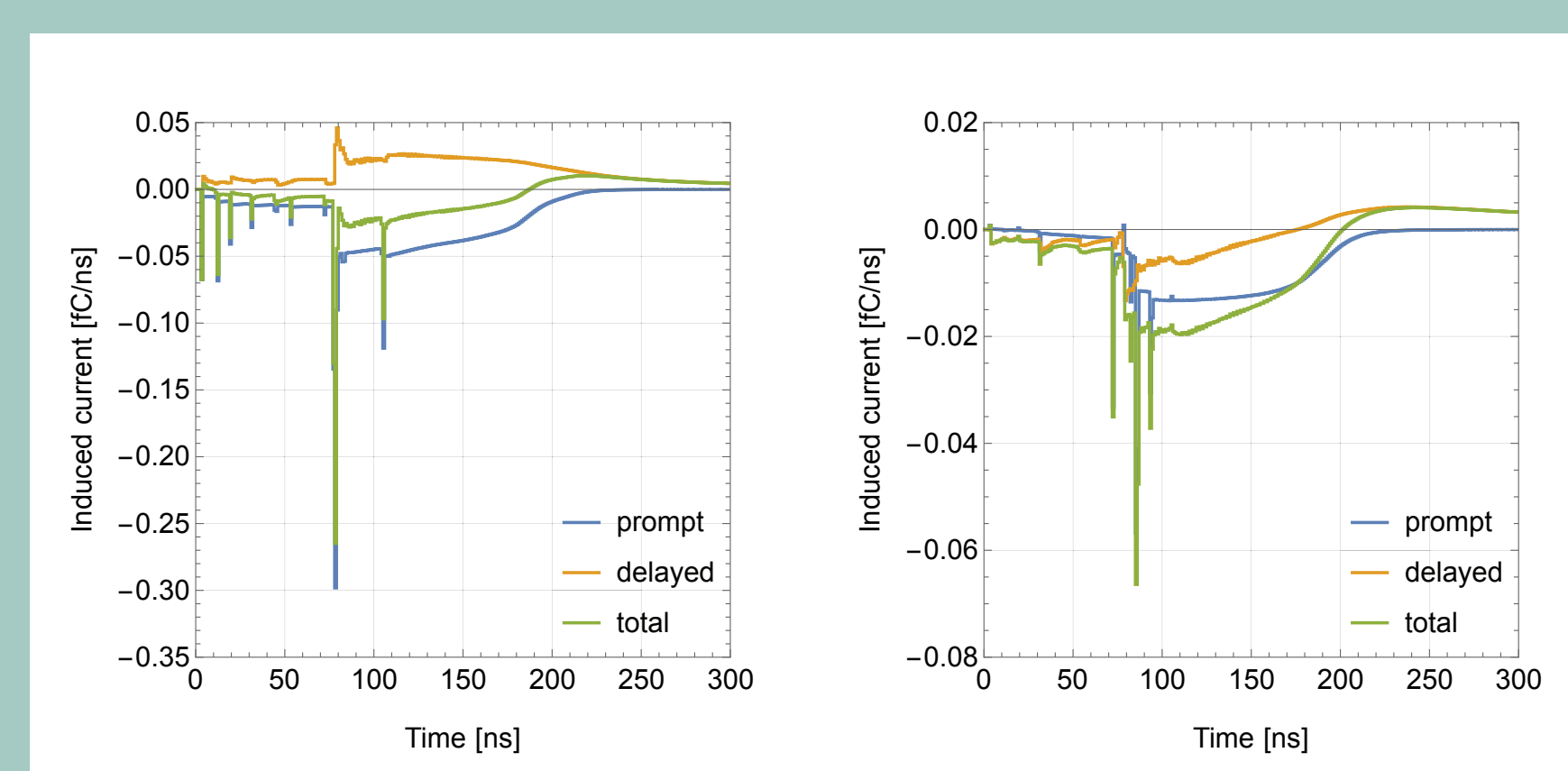


Fig. 5: Induced current on the leading and neighboring x-strips due to the movement of the charges (prompt) and resistive material (delayed).

4 Results

By employing an extended form of the Ramo-Shockley theorem, we studied the induced current response of various devices. These models were systematically validated against toy-model results and experimental data. Notably, a benchmark was conducted using the resistive strip MM [9], demonstrating strong agreement between simulations and experimental findings.

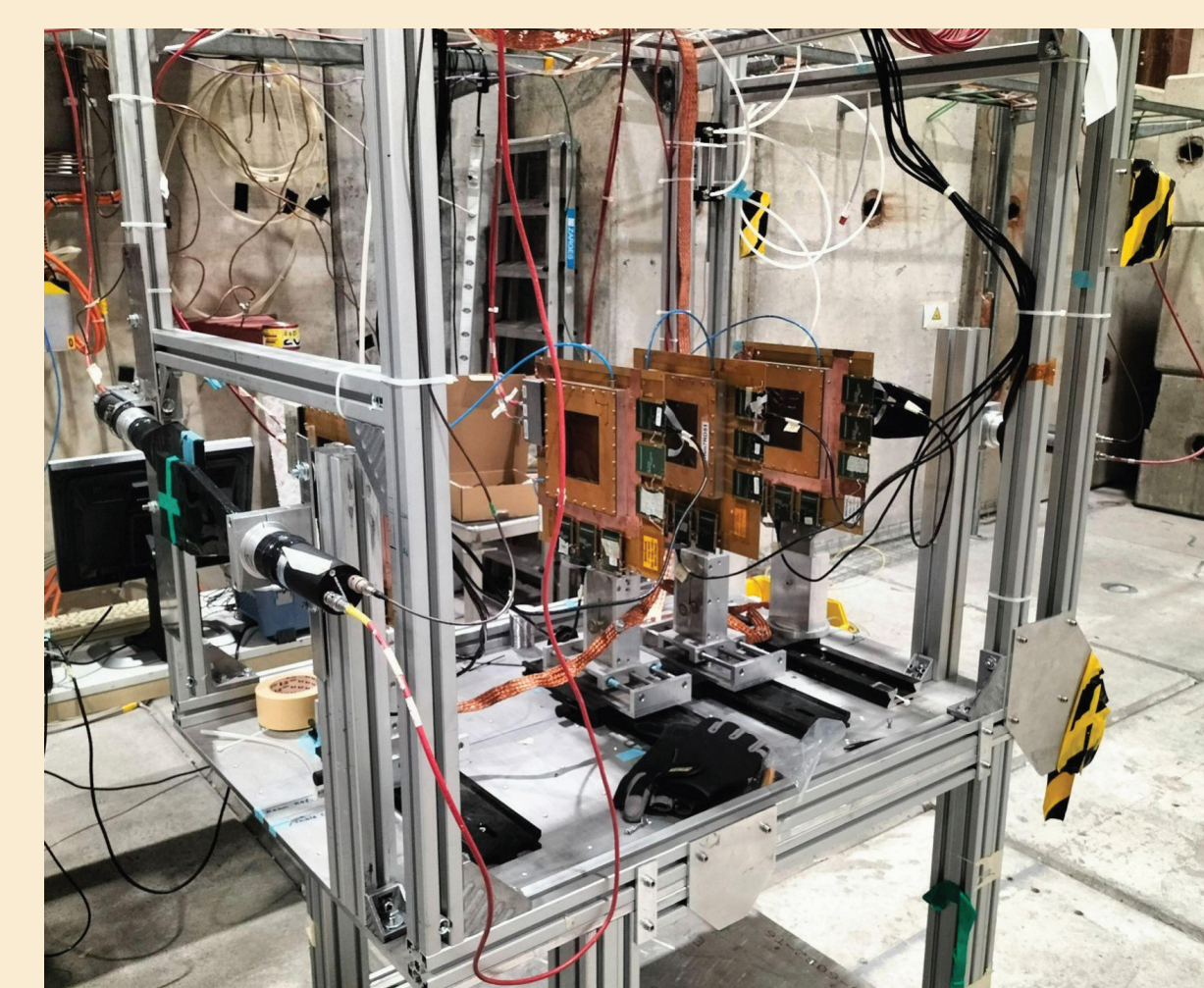


Fig. 6: Image of the test beam tracker at the CERN SPS H4 beamline for the measurement of the average current response of the resistive strip MM.

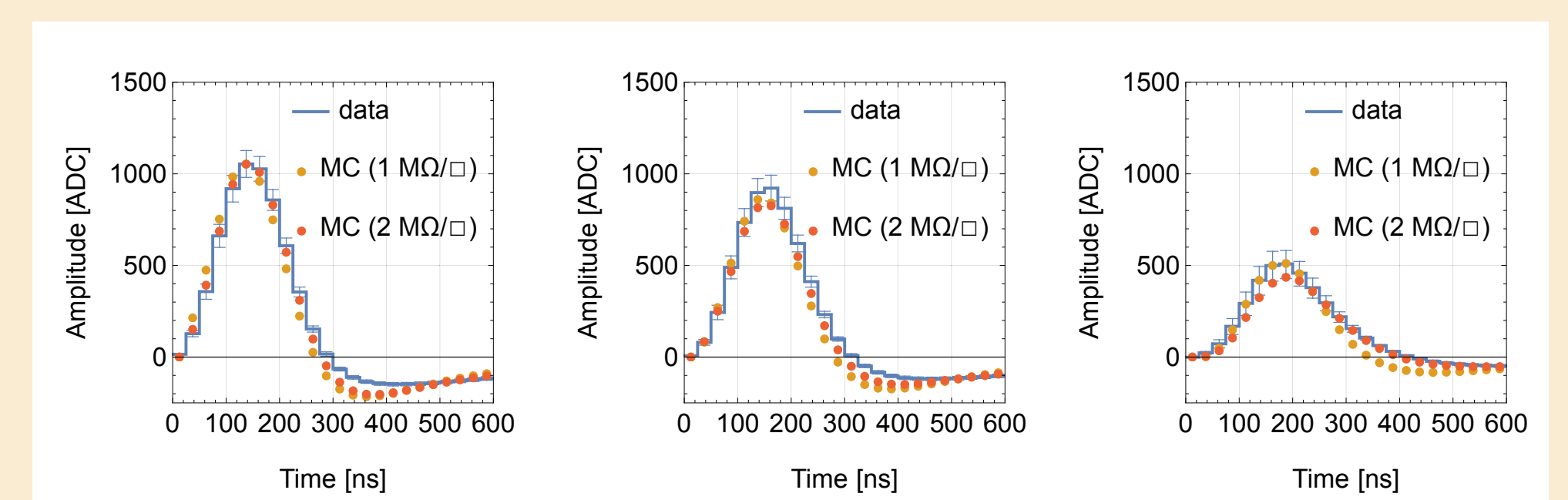


Fig. 7: Comparison between the simulated and measured average induced current of three adjacent x-strips in a resistive strip MM.

5 Conclusion

Through simulation and measurement, we have explored novel solutions in MRPCs, Micro Pattern Gaseous Detectors, and solid-state sensors incorporating resistive elements [10]. These studies can be employed to advance the design and optimization of future detectors and be tailored to meet the specific demands of HEP experiments.

References

[1] Garfield++, <https://garfieldpp.web.cern.ch> (2024)
[2] G. Giacomini et al., JINST 14 (2019) 09, P09004
[3] W. Shockley, J. Appl. Phys. 9 (1938) 635
[4] S. Ramo, Proc. Ire. 27 (1939) 584

[5] E. Gatti et al., NIM in Phys. Res. 193 (1982) 651
[6] W. Riegler, NIM-A 535 (2004), 287-293
[7] COMSOL 6.2, <https://www.comsol.ch> (2024)

Resulting works

[8] D. Janssens et al., NIM-A 1040 (2022) 167227
[9] D. Janssens et al., JINST 18 (2023) 08, C08010
[10] D. Janssens, Ph.D. thesis, CERN-THESIS-2023-349

